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LIFETIME OF NANO-STRUCTURED BLACK SILICON FOR PHOTOVOLTAIC APPLICATIONS

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ABSTRACT: In this work, we present recent results of lifetime optimization for nano-structured black silicon and its photovoltaic applications. Black silicon nano-structures provide significant reduction of silicon surface reflection due to highly corrugated nanostructures with excellent light trapping properties. We applied reactive ion etching technology at -20°C to create nano-structures on silicon samples and obtained an average reflectance below 0.5%. For passivation purposes, we used 37 nm ALD Al_2O_3 films. Lifetime measurements resulted in 1220 μs and to 4170 μs for p- and n-type CZ silicon wafers, respectively. This is promising for use of black silicon RIE nano-structuring in a solar cell process flow.

Keywords: c-Si, black silicon, ALD Al_2O_3 , passivation, lifetime, light trapping, nano-structured silicon

1 INTRODUCTION

Nano-textured silicon, known as black silicon, is currently a subject of great interest in photovoltaics [1–4, 5]. It has extremely low surface reflectance, in some cases below 1%, in a broad range of wavelengths and incident angles even with a simple antireflective coating [6, 7]. Reactive plasma etching is a most promising alternative to any other silicon texturing method like wet etching [8–11], plasma immersion ion implantation etching, metal nanoparticles assisted etching and laser induced etching [12–15]. Key advantages of dry plasma silicon structuring are no usage of toxic chemicals, easy morphology control of structure size and shape, less silicon waste and mask-less processing. Solar cells with improved light trapping nano-structures show improved characteristics, such as high open circuit voltage and large short circuit current. However, surface-texturing methods like RIE also induce surface damage and potentially contamination, and therefore increased surface recombination velocity resulting in poor performance of nano-structured solar cells [3, 5, 16, 17]. Thus, effective surface passivation of nano-textured surfaces and optimization of the texturing process towards reduction of surface defect damage is required for further black silicon application in photovoltaics [18–22]. Atomic layer deposition (ALD) of Al_2O_3 is one of the best methods for black silicon passivation, since it has conformal coverage of plane and corrugated surfaces. Thermal ALD of Al_2O_3 leads to high chemical interface quality on crystalline silicon, low density of defect states, and the strongest known field effect due to fixed negative charges [18, 20, 21, 23–32].

2 EXPERIMENT

2.1 Sample Details and Black Silicon Etching

Black silicon nanostructuring was realized on Czochralski (CZ) mono-crystalline Si 4" (100) n- and p-type (1-20 Ωcm) wafers with thickness 350 μm by mask-less reactive ion etching (RIE) in SF_6 and O_2 inductively coupled plasma at -20°C in DRIE SPTS Pegasus (Fig.1). Prior to final sample preparation, the RIE process was optimized: platen power was reduced from 50 to 10 W to reduce kinetic energy of ions, directed towards the substrate surface; coil power was increased from 2500 to

3000 W to increase homogenous ion plasma density and maintain a stable etch rate; aspect ratio of nanostructures was controlled via the low gas pressure (38 mTorr) which determined the directionality of the ions and the physical etching components by reducing the mean free path of the plasma species; average flow of SF_6 gas (70 sccm) allowed to a stable Si etch rate and high O_2 flow (100 sccm) allowed to passivate Si surface and reduce etch rate. The first samples had shown low lifetime after ALD Al_2O_3 passivation and are not referred in this report. For conducting the experiment we used six silicon wafers of n- and p-type: two wafers had single side RIE processing for 16 min, another two wafers had double sided RIE processing for 16 min on each side and the last two wafer were kept as plain polished references.

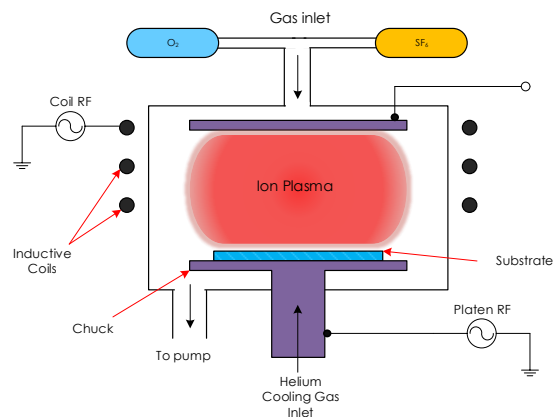


Figure 1: Schematic of inductive coupled plasma system used for RIE

The black silicon nano-structuring process was conducted in the following order as shown on Fig. 2. A sample wafer was loaded in to the ICP RIE chamber and cooled to -20°C . SF_6 gas was supplied to the chamber and fluorine radicals rapidly attacked the silicon and destroyed native oxide on top of the wafer forming volatile SiF_4 . In the next step, oxygen was supplied to the chamber. Oxygen radicals form silicon-oxyfluorine $\text{SiF}_4 + \text{O}^* = \text{SiO}_x\text{F}_y$ at low temperature (-20°C). SiO_xF_y acts as an etch stop for F^* and passivated sample surface. Horizontal planes were more

intensively bombarded by ions from plasma while on the vertical sidewalls the ion bombardment was weaker due to directionality of the plasma ions and the sidewalls therefore remained protected from chemical etching by fluorine radical [1-2].

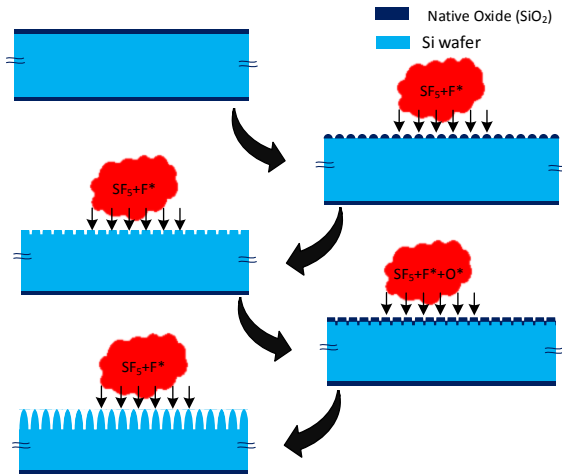


Figure 2: Schematic view of black silicon nanostructures formation

2.2 Surface cleaning and ALD Al₂O₃ passivation

After RIE all samples were cleaned in standard RCA cleaning solutions, RCA1 and RCA2, each with a subsequent HF-dip, rinsed in deionized water and spin dried. Subsequently, wafers were coated with 380 cycles of ALD Al₂O₃ synthesized from trimethylaluminium (TMA) and H₂O. For reference purposes two polished wafers (p- and n-type) were also included in ALD Al₂O₃ passivation procedure. The passivation layers were activated by post-deposition in-situ annealing in N₂ ambient at 375-390 °C for 30 min. The resulting Al₂O₃ thickness of 37 nm was measured from polished reference samples using ellipsometry. Charge carrier lifetime was measured after annealing with the microwave detected photoconductivity (MDP) method in transient as well as in injection dependent single point modes, and lifetime mapping mode using a MDPmap setup from Freiburg Instruments.

3 RESULTS AND DISCUSSIONS

3.1 Black Silicon SEM Morphology Study

In Fig. 3 scanning electron microscope (SEM) images of the resulting black silicon nano-structures are shown without Al₂O₃ coating. The nanostructure topology consists of slightly rounded conical-like hillocks with average height of 500 nm and average spacing of 250 nm. There is a slight variation in the dimensions of the surface structures. The height of the nanostructures was controlled by etching time with an average etch rate of 30 nm/min.

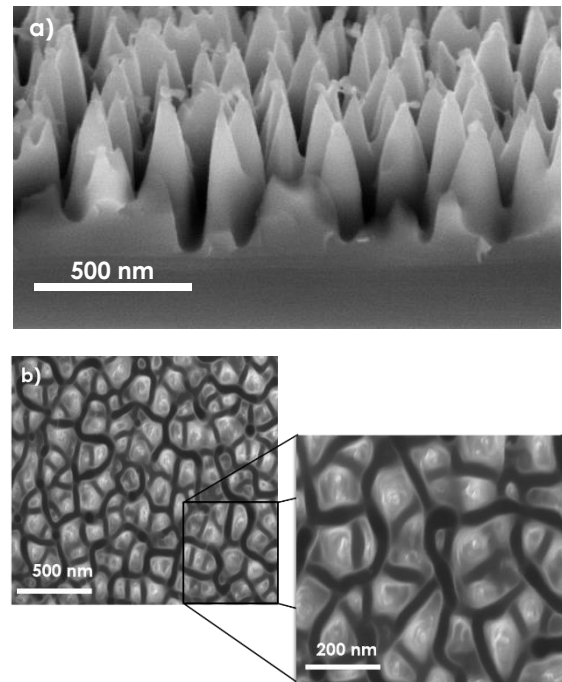


Figure 3: SEM image of the black silicon nano-structure topology processed with plasma assisted mask-less reactive ion etching: a) side view with scale 500 nm, b) top views with scale 500 nm and 200 nm

3.2 Reflectance

The main purpose of nanostructuring is to reduce reflectance and improve light trapping properties of the Si surface [3, 33]. The spectral reflectance of black silicon and polished samples were measured in the wavelength range from 500 to 1100 nm. Fig. 4 shows the reflectance of the samples as a function of wavelength. Photographic images are inserted in the reflectance figure to illustrate the difference between polished and nanostructured samples. It can be seen that polished silicon wafer in average has reflectance of 30%, while the black silicon sample has reflectance below 1% up to 1000 nm. Above 1000 nm the reflectance still remains low but shows a slight increase up to 5% which is still much lower than that of the polished wafer, and this long wavelength reflectance may partly be due to reflectance of the chuck below the silicon sample.

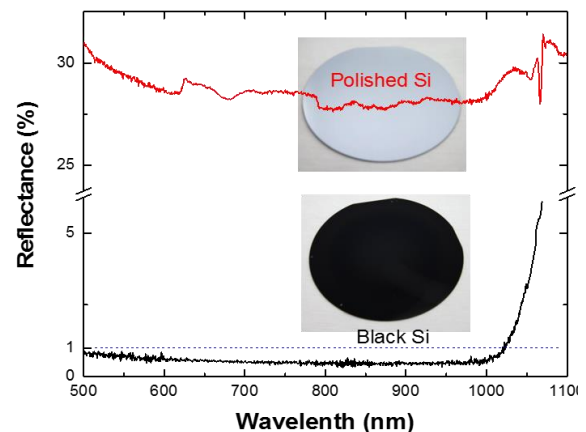


Figure 4: Experimental reflectance spectra of polished and black silicon without Al₂O₃ coating

3.3 Minority Carrier Lifetime

Fig. 5 shows measured effective minority carrier lifetime for p- and n-type wafers for polished as well as for nano-textured samples. MDP measurements were conducted with a MDPmap setup from Freiberg Instruments to determine the effective carrier lifetimes as a function of injection level. The effective minority carrier lifetime is a figure of merit to estimate surface recombination and surface damage [18, 21, 25, 34, 35].

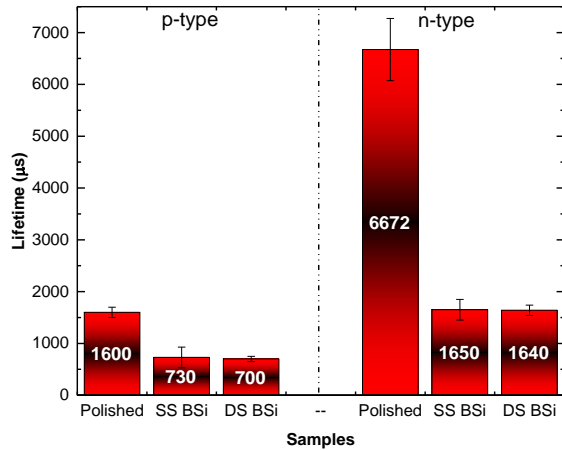


Figure 5: Comparative graph of average lifetime wafer mapping values with standard deviation for p- and n-type silicon samples with polished, single side nanostructured and double side nanostructured black silicon, passivated with ALD Al₂O₃ 37 nm film. Legend: SS BSi - single side nanostructured black silicon, DS BSi - double side nanostructured black silicon

For p-type Si wafers, the lifetime difference between polished and textured samples is a factor of two. For some samples we have recorded a lifetime approaching 1 ms and higher, however to report these results additional testing is required. Injection dependent lifetime for p-type samples shown in Fig. 6 confirms stability of above results. A similar tendency is present for n-type samples, however lifetime difference between polished and nanostructured samples is in that case a factor of four.

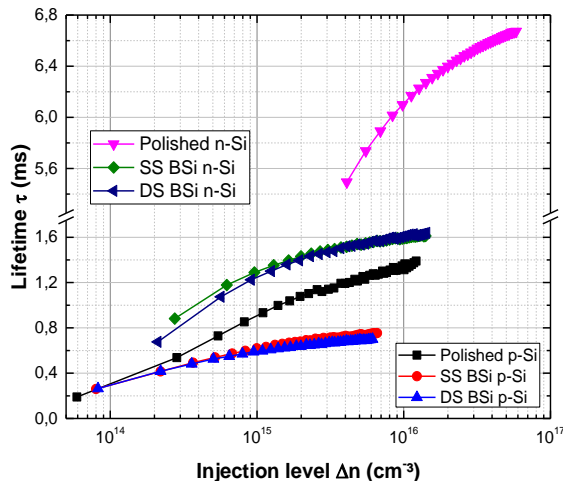


Figure 6: Lifetime dependency on injection level

The surface recombination velocity was calculated from

effective minority carrier lifetime from the equation shown in Fig. 6 [25].

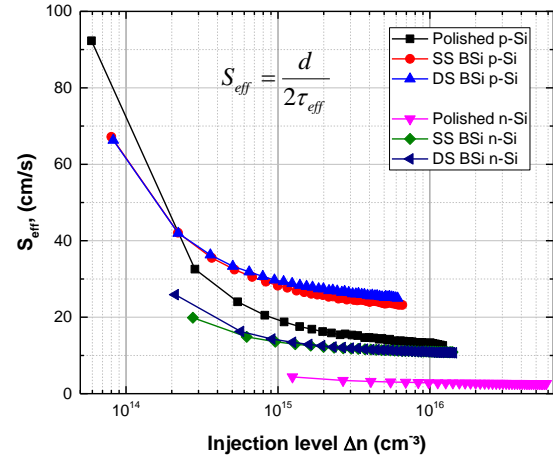


Figure 7: Surface recombination velocity dependencies on injection level

where d is the wafer thickness, τ_{eff} is the measured effective lifetime. Fig. 7 shows the calculated surface recombination velocity as a function of injection level.

4 CONCLUSION

We have presented recent results of effect of reactive ion process optimization for improvement of minority carrier lifetime. The optimized RIE recipe with reduced ion damage of the surface allows us to achieve comparatively high effective lifetime for n- and p-type wafers and for single and double side nano-textured samples. For further investigation of electro-optical properties all samples were passivated with Al₂O₃ and annealed at 375-390°C for 30 min. The surface morphology of textured samples was studied using SEM, and the optical reflectance was measured with an integrated sphere in the range of 500-1100 nm. Reflectance measurements allow us to evaluate the antireflective properties of nanostructures. With the plasma-assisted mask-less etching method we achieved broad spectral reflectance below 0.5%. Finally, the effective lifetime was measured on all textured and reference polished samples to evaluate the passivation effect and to estimate surface recombination velocity. Our overall results are promising for black silicon fabrication and lifetime improvement to facilitate incorporation in solar cell fabrication.

5 REFERENCES

- [1] Koynov, S., Brandt, M. S. & Stutzmann, M. Black thin film silicon. J. Appl. Phys. 110, 043537 (2011).
- [2] Kroll, M. et al. Black silicon for solar cell applications. Proc. SPIE 8438, 843817 (2012).
- [3] Koynov, S., Brandt, M. S. & Stutzmann, M. Black nonreflecting silicon surfaces for solar cells. Appl. Phys. Lett. 88, 203107 (2006).
- [4] Otto, M. et al. Black Silicon Photovoltaics. Adv. Opt. Mater. 3, 147-164 (2015).
- [5] Davidsen, R. S. et al. Black silicon laser-doped selective emitter solar cell with 18.1% efficiency.

- Sol. Energy Mater. Sol. Cells 144, 740–747 (2016).
- [6] Koynov, S., Brandt, M. S. & Stutzmann, M. Black thin film silicon. *J. Appl. Phys.* 110, 043537 (2011).
- [7] Raghunathan, D. Black silicon for higher efficiency in solar cells. *Appl. Mech. Mater.* 787, 92–96 (2015).
- [8] Huang, Z., Geyer, N., Werner, P., De Boor, J. & Gösele, U. Metal-assisted chemical etching of silicon: A review. *Advanced Materials* 23, 285–308 (2011).
- [9] Koynov, S., Brandt, M. S. & Stutzmann, M. Black nonreflecting silicon surfaces for solar cells. *Appl. Phys. Lett.* 88, 203107 (2006).
- [10] Liu, Y. et al. Nanostructure formation and passivation of large-area black silicon for solar cell applications. *Small* 8, 1392–1397 (2012).
- [11] Lu, Y.-T. & Barron, A. R. Nanopore-type black silicon anti-reflection layers fabricated by a one-step silver-assisted chemical etching. *Phys. Chem. Chem. Phys.* 15, 9862–70 (2013).
- [12] Iyengar, V. V. et al. Properties of ultrafast laser textured silicon for photovoltaics. *Sol. Energy Mater. Sol. Cells* 95, 2745–2751 (2011).
- [13] Kontermann, S., Gimpel, T., Baumann, A. L. L., Guenther, K.-M. M. & Schade, W. Laser processed black silicon for photovoltaic applications. *Energy Procedia* 27, 390–395 (2012).
- [14] Sarnet, T., Carey, J. E. & Mazur, E. From black silicon to photovoltaic cells, using short pulse lasers. *AIP Conference Proceedings* 1464, 219–228 (2012).
- [15] Schütz, V., Horn, A., Nagel, H. & Stute, U. Black silicon solar cell processing with high repetitive laser systems. 27th European Photovoltaic Solar Energy Conference and Exhibition 1864–1866 (2012).
- [16] Oh, J., Yuan, H.-C. & Branz, H. M. An 18.2%-efficient black-silicon solar cell achieved through control of carrier recombination in nanostructures. *Nat. Nanotechnol.* 7, 743–748 (2012).
- [17] Savin, H. et al. Black silicon solar cells with interdigitated back-contacts achieve 22.1% efficiency. *Nat. Nanotechnol.* 10, 1–6 (2015).
- [18] Dou, B. et al. Surface passivation of nanotextured silicon solar cells by atomic layer deposited Al_2O_3 films. *J. Appl. Phys.* 114, 174301 (2013).
- [19] Hsu, C.-H. et al. Fabrication and characteristics of black silicon for solar cell applications: An overview. *Mater. Sci. Semicond. Process.* (2014). doi:10.1016/j.mssp.2014.02.005
- [20] Otto, M. et al. Passivation of different black silicon surfaces by ALD deposited Al_2O_3 . 2013 IEEE 39th Photovoltaic Specialists Conference (PVSC) 1277–1279 (IEEE, 2013). doi:10.1109/PVSC.2013.6744374
- [21] Otto, M. et al. Passivation of optically black silicon by atomic layer deposited Al_2O_3 . *Energy Procedia* 38, 862–865 (2013).
- [22] Zhao, Z., Zhang, B., Li, P., Guo, W. & Liu, A. Effective passivation of large area black silicon solar cells by $\text{SiO}_2/\text{SiN}_x/\text{H}$ stacks. *Int. J. Photoenergy* 2014, 1–6 (2014).
- [23] Otto, M. et al. Extremely low surface recombination velocities in black silicon passivated by atomic layer deposition. *Appl. Phys. Lett.* 100, 191603 (2012).
- [24] Repo, P. et al. Passivation of black silicon boron emitters with atomic layer deposited aluminium oxide. *Phys. status solidi - Rapid Res. Lett.* 7, 950–954 (2013).
- [25] Repo, P. et al. Effective passivation of black silicon surfaces by atomic layer deposition. *IEEE J. Photovoltaics* 3, 90–94 (2013).
- [26] Wang, W.-C. et al. Surface passivation of efficient nanotextured black silicon solar cells using thermal atomic layer deposition. *ACS Appl. Mater. Interfaces* 5, 9752–9 (2013).
- [27] Benick, J. et al. Effect of a post-deposition anneal on $\text{Al}_2\text{O}_3/\text{Si}$ interface properties. *Photovolt. Spec. Conf. (PVSC)*, 2010 35th IEEE 891–896 (2010). doi:10.1109/PVSC.2010.5614148
- [28] Bordihn, S. et al. Impact of the deposition and annealing temperature on the silicon surface passivation of ALD Al_2O_3 films. *Energy Procedia* 27, 396–401 (2012).
- [29] Dingemans, G. & Kessels, W. M. M. Status and prospects of Al_2O_3 -based surface passivation schemes for silicon solar cells. *J. Vac. Sci. Technol. A Vacuum, Surfaces, Film.* 30, 040802 (2012).
- [30] Dingemans, G. & Kessels, W. M. M. Aluminum oxide and other ALD materials for Si surface passivation. *ECS Trans.* 41, 293–301 (2011).
- [31] Kotipalli, R. et al. Passivation effects of atomic-layer-deposited aluminum oxide. *EPJ Photovoltaics* 4, (2013).
- [32] Schmidt, J., Werner, F., Veith, B. & Zielke, D. Industrially relevant Al_2O_3 deposition techniques for the surface passivation of Si solar cells. *Photovolt. Sol.* 4–7 (2010). doi:10.4229/25thEUPVSEC2010-2AO.1.6
- [33] Zhu, J., Yu, Z., Fan, S. & Cui, Y. Nanostructured photon management for high performance solar cells. *Materials Science and Engineering R: Reports* 70, 330–340 (2010).
- [34] Sinton, R. A. & Cuevas, A. Contactless determination of current–voltage characteristics and minority-carrier lifetimes in semiconductors from quasi-steady-state photoconductance data. *Appl. Phys. Lett.* 69, 2510 (1996).
- [35] Stephens, A. W. & Green, M. A. Novel method for minority-carrier mobility measurement using photoconductance decay with chemically passivated and plasma damaged surfaces. *J. Appl. Phys.* 80, 3897 (1996).